

Pb Free Plating Product

RHRP15120



15 Ampere, 1200 Volt SwitchMode Single Fast Recovery Epitaxial Diode

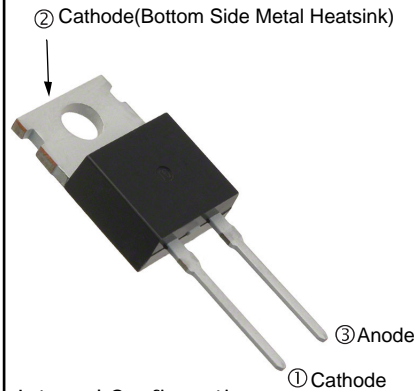
APPLICATION

- Freewheeling, Snubber, Clamp
- Inversion Welder
- PFC
- Plating Power Supply
- Ultrasonic Cleaner and Welder
- Converter & Chopper
- UPS

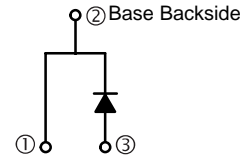
PRODUCT FEATURE

- Ultrafast Recovery Time
- Soft Recovery Characteristics
- Low Recovery Loss
- Low Forward Voltage
- High Surge Current Capability
- Low Leakage Current

TO-220AC/TO-220C-2P



Internal Configuration



GENERAL DESCRIPTION

RHRP15120 using the latest FRED FAB process(planar passivation chip) with ultrafast and soft recovery characteristic.

ABSOLUTE MAXIMUM RATINGS

$T_C = 25^\circ\text{C}$ unless otherwise specified

| Symbol | Parameter/Test Conditions | | Values | Unit |
|---------------|--------------------------------------|---------------------------------------------------------------------|-------------|---------------------------|
| V_R | Maximum D.C. Reverse Voltage | | 1200 | V |
| V_{RRM} | Maximum Repetitive Reverse Voltage | | | |
| $I_{F(AV)}$ | Average Forward Current | $T_C = 100^\circ\text{C}$ | 15 | A |
| $I_{F(RMS)}$ | RMS Forward Current | $T_C = 100^\circ\text{C}$ | 21 | |
| I_{FSM} | Non Repetitive Surge Forward Current | $T_J = 45^\circ\text{C}, t = 10\text{ms}, 50\text{Hz}, \text{Sine}$ | 150 | |
| P_D | Power Dissipation | | 125 | W |
| T_J | Junction Temperature | | -55 to +150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature Range | | -55 to +125 | $^\circ\text{C}$ |
| Torque | Module to Sink | Recommended (M3) | 1.1 | Nm |
| R_{thJC} | Junction to Case Thermal Resistance | | 1.0 | $^\circ\text{C}/\text{W}$ |
| Weight | | | 2.5 | g |

ELECTRICAL CHARACTERISTICS

$T_C = 25^\circ\text{C}$ unless otherwise specified

| Symbol | Parameter/Test Conditions | | Min. | Typ. | Max. | Unit |
|-----------|----------------------------------|----------------------------------------------------------------------------------------------------|------|------|------|---------------|
| I_{RM} | Maximum Reverse Leakage Current | $V_R = 1200\text{V}$ | | | 10 | μA |
| | | $V_R = 1200\text{V}, T_J = 125^\circ\text{C}$ | | | 1 | mA |
| V_F | Forward Voltage | $I_F = 15\text{A}$ | | 2.8 | 3.2 | V |
| | | $I_F = 15\text{A}, T_J = 125^\circ\text{C}$ | | 2.3 | | |
| t_{rr} | Reverse Recovery Time | $(I_F = 1\text{A}, dI_F/dt = -200\text{A}/\mu\text{s}, V_R = 30\text{V})$ | | 25 | 30 | ns |
| t_{rr} | Reverse Recovery Time | $(I_F = 0.5\text{A}, I_R = 1\text{A}, I_{RR} = 0.25\text{A})$ | | 35 | 40 | ns |
| t_{rr} | Reverse Recovery Time | $I_F = 15\text{A}, V_R = 600\text{V}, dI_F/dt = -200\text{A}/\mu\text{s}$ | | 72 | | ns |
| I_{RRM} | Maximum Reverse Recovery Current | $dI_F/dt = -200\text{A}/\mu\text{s}$ | | 5 | | A |
| t_{rr} | Reverse Recovery Time | $I_F = 15\text{A}, V_R = 600\text{V}, dI_F/dt = -200\text{A}/\mu\text{s}, T_J = 125^\circ\text{C}$ | | 240 | | ns |
| I_{RRM} | Maximum Reverse Recovery Current | $dI_F/dt = -200\text{A}/\mu\text{s}, T_J = 125^\circ\text{C}$ | | 7.5 | | A |

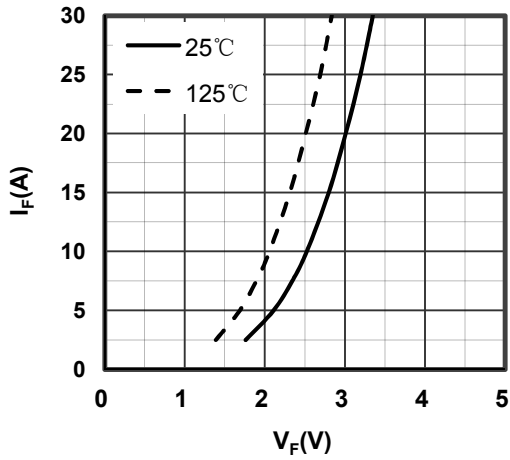


Figure 1. Forward Voltage Drop vs Forward Current

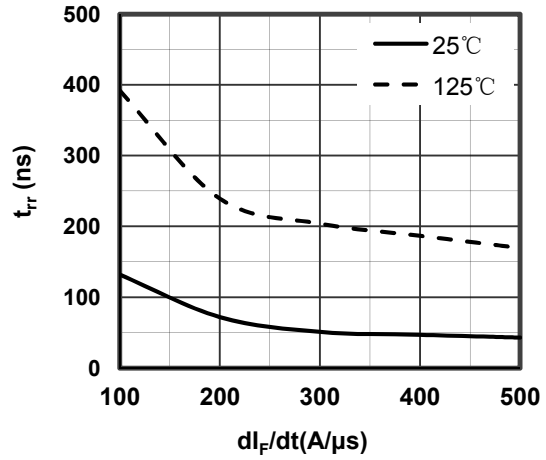


Figure 2. Reverse Recovery Time vs dI_F/dt

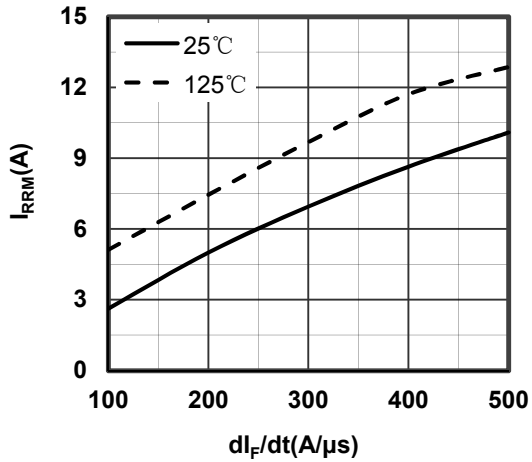


Figure 3. Reverse Recovery Current vs dI_F/dt

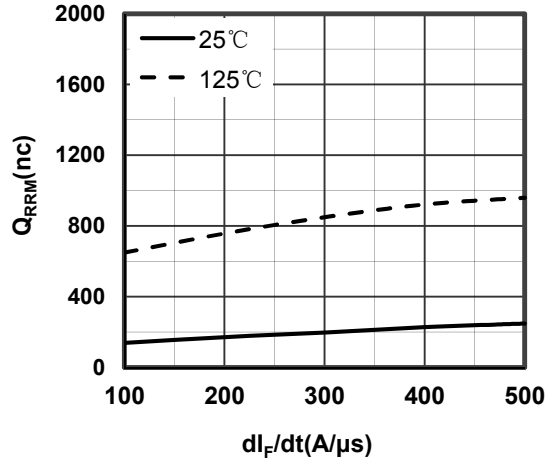


Figure 4. Reverse Recovery Charge vs dI_F/dt

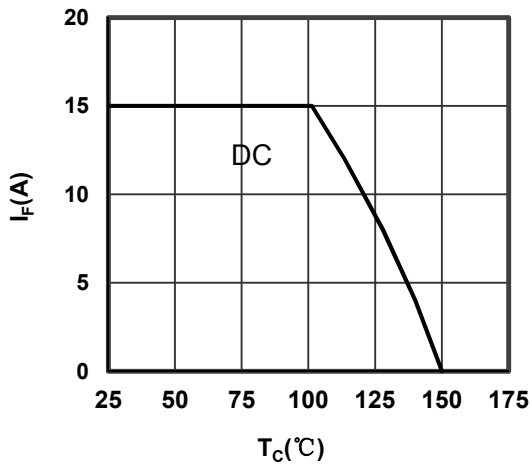


Figure 5. Forward current vs Case temperature

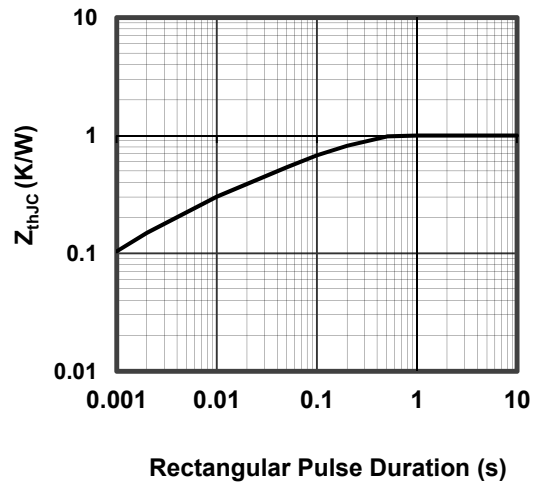


Figure 6. Transient Thermal Impedance

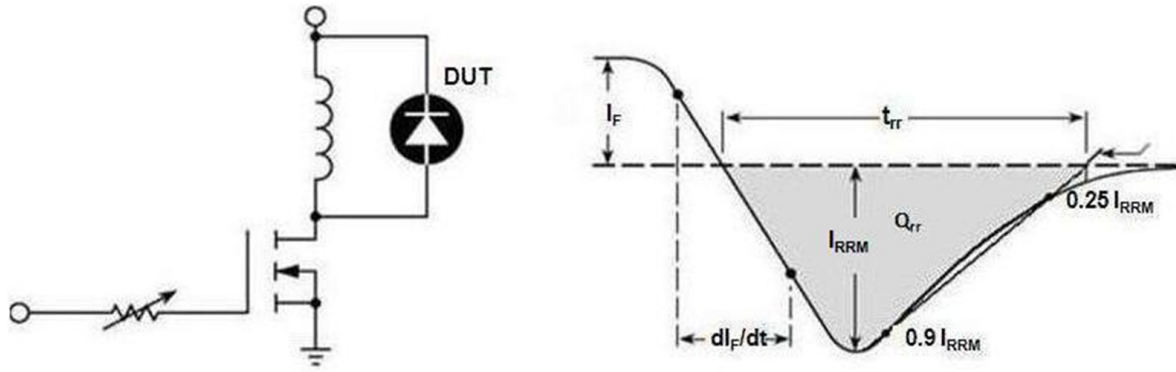
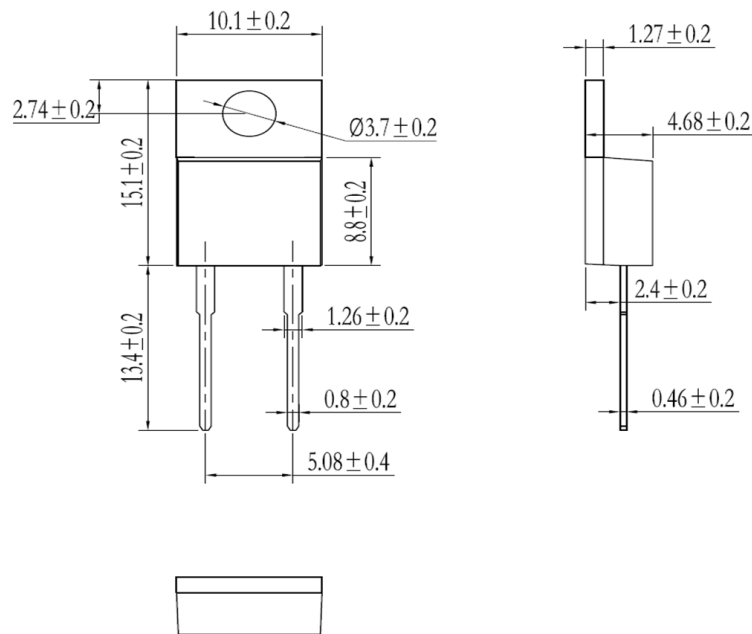


Figure 7. Diode Reverse Recovery Test Circuit and Waveform



Dimensions in (mm)
Figure 8. Package Outline